

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI ULBM10** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.5 A
V_{CB0}	36 V
V_{CEO}	16 V
V_{CES}	36 V
V_{EBO}	4.0 V
P_{DISS}	58 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	7.0 °C/W

PACKAGE STYLE .280 4L STUD

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10682

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 20 mA	16			V
BV_{CES}	I _C = 25 mA	36			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CEO}	V _{CB} = 15 V			2.0	mA
I_{CES}	V _{CE} = 10 V			3.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		---	---
C_{ob}	V _{CB} = 12.5 V f = 1.0 MHz			25	pF
P_G	V _{CC} = 12.5 V P _{OUT} = 10 W f = 470 MHz	7.0			dB
η_C			60		%